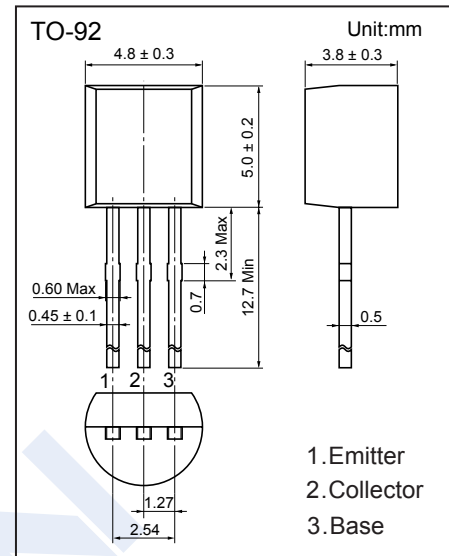


PNP Transistors

KTA1266

■ Features

- Excellent hFE Linearity
- Low Noise
- Complementary to KTC3198

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-50	V
Collector - Emitter Voltage	V_{CE0}	-50	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-150	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100\mu\text{A}$, $I_E = 0$	-50			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1\text{mA}$, $I_B = 0$	-50			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100\mu\text{A}$, $I_C = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -50\text{V}$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = 5\text{V}$, $I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}$, $I_B = -10\text{mA}$			-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}$, $I_B = -10\text{mA}$			-1.1	
DC current gain	$h_{FE(1)}$	$V_{CE} = -6\text{V}$, $I_C = -2\text{mA}$	70		400	
	$h_{FE(2)}$	$V_{CE} = -6\text{V}$, $I_C = -150\text{mA}$	25			
Noise figure	NF	$V_{CE} = -6\text{V}$, $I_C = -0.1\text{mA}$, $f = 1\text{KHz}$, $R_g = 10\text{K}\Omega$			10	dB
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$			7	pF
Transition frequency	f_T	$V_{CE} = -10\text{V}$, $I_C = -1\text{mA}$	80			MHz

■ Classification of $h_{FE(1)}$

Type	KTA1266-O	KTA1266-Y	KTA1266-G
Range	70-140	120-240	200-400

PNP Transistors

KTA1266

■ Typical Characteristics

